

No.2807

## 2SA1654/2SC4361

PNP/NPN Epitaxial Planar Silicon Transistors

### Switching Applications (with Bias Resistance)

**Applications**

- Switching circuit, inverter circuit, interface circuit, driver circuit

**Features**

- On-chip bias resistance (R1 = 4.7kΩ, R2 = 10kΩ)

( ) : 2SA1654

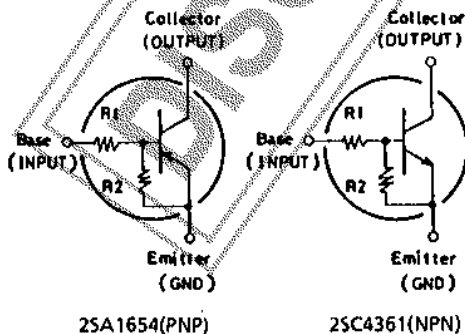
**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	(-)150	V
Collector to Emitter Voltage	V <sub>CEO</sub>	(-)150	V
Emitter to Base Voltage	V <sub>EBO</sub>	(-)6	V
Collector Current	I <sub>C</sub>	(-)100	mA
Collector Current (Pulse)	I <sub>CP</sub>	(-)200	mA
Collector Dissipation	P <sub>C</sub>	300	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

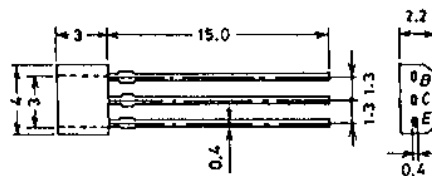
			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = (-)40V, I <sub>E</sub> = 0			(-)0.1	μA
Collector Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> = (-)40V, I <sub>B</sub> = 0			(-)0.5	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = (-)5V, I <sub>C</sub> = 0	(-)262	(-)340	(-)485	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = (-)5V, I <sub>C</sub> = (-)10mA	50			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = (-)10V, I <sub>C</sub> = (-)5mA		250		MHz
				(200)		MHz
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> = (-)10V, f = 1MHz		3.7		pF
				(5.5)		pF
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = (-)10mA, I <sub>B</sub> = (-)0.5mA	(-)0.1	(-)0.3		V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = (-)10μA, I <sub>E</sub> = 0	(-)50			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = (-)100μA, R <sub>BE</sub> = ∞	(-)50			V
Input OFF-State Voltage	V <sub>I(off)</sub>	V <sub>CE</sub> = (-)5V, I <sub>C</sub> = (-)100μA	(-)0.7	(-)0.85	(-)0.95	V
Input ON-State Voltage	V <sub>I(on)</sub>	V <sub>CE</sub> = (-)0.2V, I <sub>C</sub> = (-)10mA	(-)0.95	(-)1.3	(-)2.0	V
Input Resistance	R1		3.3	4.7	6.1	kΩ
Resistance Ratio	R1/R2			0.47		

**Electrical Connection**



**Case Outline 2033**

(unit : mm)

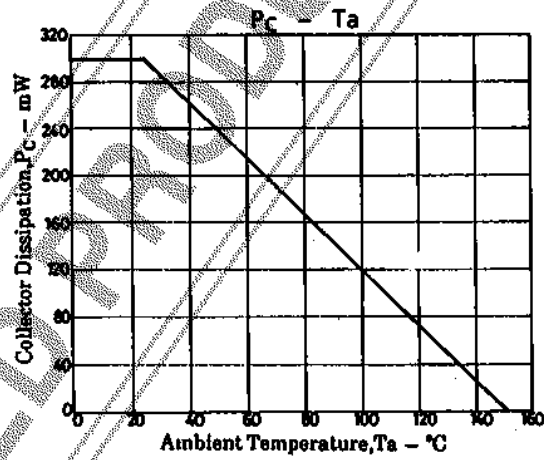
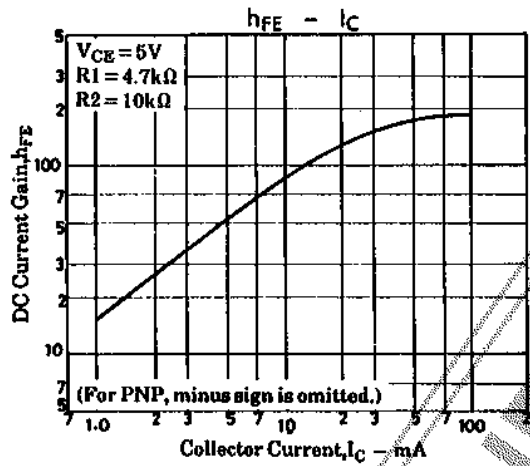
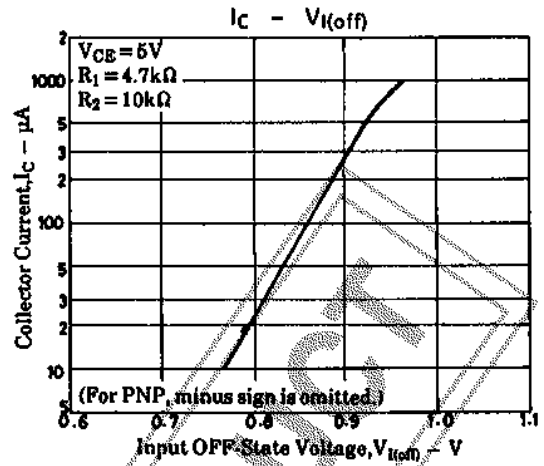
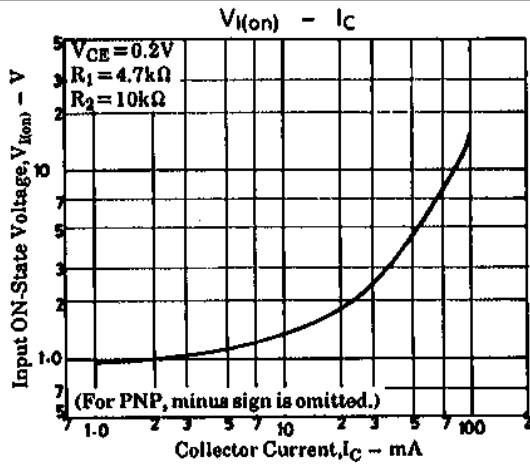


B: Base  
C: Collector  
E: Emitter  
SANYO: SPA

Specifications and information herein are subject to change without notice.

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DISCONTINUED